

Examination's Log

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AN 1989-155241 [21] WPIDS
DNN N1989-118218 DNC C1989-068850
TI Sputtering clad target material - comprises
target material clad through metal bonding agent to copper
substrate contg. e.g. cadmium, iron etc..
DC M13 U11
PA (TANI) TANAKA KIKINZOKU KOGYO KK
CYC 1
PI JP 01096376 A 19890414 (198921)* 3p
ADT JP 01096376 A JP 1987-251177 19871005
PRAI JP 1987-251177 19871005
AB JP 01096376 A UPAB: 19930923
A sputtering clad target material comprises
target material clad through metal bonding agent to a more than
99.7% purity Cu substrate including at least one of Cd, Fe, Co,
Ni, Ti, W, V, Si, Zr, Bi, Ga, Ge, Pt, Pd, Rh, Ru, Ir, Os, Au and Ag
100-3,000 ppm in total. Substrate contacting backing plate is prevented
from being pressure-bonded.
1-3/3